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- (71) Applicant: MOTOROLA, INC. Schaumburg, IL 60196 (US)
- (72) Inventors:
 - · Boeck, Bruce Allen Austin, Texas 78759 (US)

- · Wetzel, Jeff Thomas Austin, Texas 78735 (US)
- · Sparks, Terry Grant Austin, Texas 78754 (US)
- (74) Representative:

Gibson, Sarah Jane et al Motorola

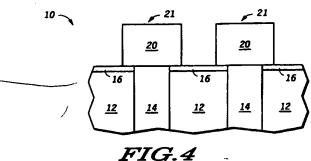
European Intellectual Property Operations Midpoint

Alencon Link

Basingstoke, Hampshire RG21 7PL (GB)

(54)Method for manufacturing a semiconductor structure comprising regions formed with low dielectric constant material

(57)An interconnect structure having a dielectric layer with low dielectric constant is formed within an integrated circuit. In one embodiment of the invention, portions of a silicon dioxide layer (18) lying adjacent to a conductive interconnect (21) are removed to expose portions of a silicon nitride etch stop layer (16). A dielectric layer (22) having a low dielectric constant is then formed overlying the conductive interconnect (21) and the exposed portions of the silicon nitride etch stop layer (16). A portion of the dielectric layer (22) is then removed to expose the top surface of the conductive interconnect (21) to leave portions of the dielectric layer (22) between adjacent conductive interconnects (21). The resulting interconnect structure has reduced crosstalk between conductive interconnects (21) while avoiding prior art disadvantages of reduced thermal dissipation and increased mechanical stress.



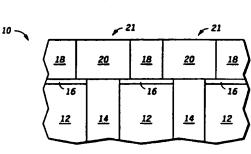
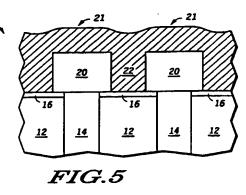
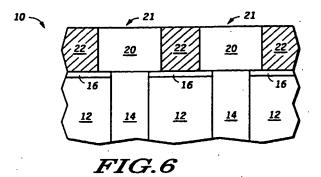


FIG.3







EUROPEAN SEARCH REPORT

Application Number EP 97 11 6851

Category	Citation of document with in of relevant passa	dication, where appropriate, ges	Rele to cla	vant aim	CLASSIFICATION OF THE APPLICATION (Int.Cl.6)
х	WO 96 19830 A (ADVANCED MICRO DEVICES IN 27 June 1996 * page 1, line 14 - line 26 * * page 2, line 11 - line 31 * * page 3, line 24 - page 5, line 19; figures 1-6 *		1-5		H01L21/768 H01L23/522 H01L23/532
x	* column 1, line 21 * column 1, line 62 * column 2, line 3 * column 5, line 11 3A,3B,4A-4C *	- line 6 * - line 55; figures - column 6, line 16;	1-3		
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A		line 27; figure 4 * line 41; figures 7,8 * line 56 *	5		H01L
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A	* page 8 *	-/	4		-
	-The present search report has t	seen drawn up for all claims	-		
	Place of search	Date of completion of the search 5. Ma.y. 1008		K14	Examiner pfenstein, P
X : par Y : par doc A : tec	BERLIN CATEGORY OF CITED DOCUMENTS ricularly relevant if taken alone ricularly relevant if combined with anoth current of the same category inhological background in-written disclosure	L : document cited t	icument, bi its in the appl for other re	ng the i ut publi ication asons	nvention shed on, or



EUROPEAN SEARCH REPORT

Application Number EP 97 11 6851

Category	Citation of document with indication, where appropriate, of relevant passages			nt CLASSIFICATION OF THE APPLICATION (Int.CI.6)
X	April 1996 * column 1, line 5 - * column 1, line 51 * column 3, line 46 figure 1 * * column 4, line 41	- column 2, line 4 *	1,3	
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		Date of completion of the search 5 May 1998		Examiner (lopfenstein, P
		T : theory or principl E : earlier patent doc after the filing dat D : document cited i L : document cited i	T: theory or principle underlying the invention E: earlier patent document, but published on, or after the filing date D: document cited in the application L: document cited for other reasons	



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Application Number EP 97 11 6851

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CATEGORY OF CITED DOCUMENTS X: particularly relevant if taken alone Y: particularly relevant if combined with another document of the same category A: technological background		T : theory or pi E : earlier pate after the fill D : document o L : document	inciple underlying the in nt document, but publis ng date afted in the application ited for other reasons	vention

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Application Number

EP 97 11 6851

CLAIMS INCURRING FEES
The present European patent application comprised at the time of filing more than ten claims.
Only part of the claims have been paid within the prescribed time limit. The present European search report has been drawn up for the first ten claims and for those claims for which claims fees have been paid, namely claim(s):
No claims fees have been paid within the prescribed time limit. The present European search report has been drawn up for the first ten claims.
LACK OF UNITY OF INVENTION
The Search Division considers that the present European patent application does not comply with the requirements of unity of invention and relates to several inventions or groups of inventions, namely:
SEE SHEET B (in case of Lack of Unity)
All further search fees have been paid within the fixed time limit. The present European search report has been drawn up for all claims.
Only part of the further search fees have been paid within the fixed time limit. The present European search report has been drawn up for those parts of the European patent application which relate to the inventions in respect of which search fees have been paid, namely claims: 1-8
None of the further search fees have been paid within the fixed time limit. The present European search report has been drawn up for those parts of the European patent application which relate to the invention first mentioned in the claims, namely claims:



LACK OF UNITY OF INVENTION SHEET B

Application Number

EP 97 11 6851

The Search Division considers that the present European patent application does not comply with the requirements of unity of invention and relates to several inventions or groups of inventions, namely:

1. Claims: 1-5

A method for isolating a first and a second laterally separated conductive regions, by filling a gap between said two regions with a dielectric layer having a dielectric constant e lower than 3.5 (Figs.1-6).

2. Claims: 6-8

A method for forming isolated separated conductive interconnects by etching interconnection trenches in portions of a second dielectric layer, said trenches also exposing air gaps formed in a previous step of patterning an underlying first dielectric layer and filling these trenches and air gaps by conductive material (Figs.7-10)

3. Claim: 9

A method for isolating adjacent separated conductive members by forming, via a spin-on process, a dielectric layer overlying the separated conductive members, without filling the space separating said members, thus bridging said space to form an air gap (Figs.11-15)

4. Claim: 10

A method for isolating adjacent separated conductive members by forming, via a PECVD process, a non-conformal dielectric layer overlying the separated conductive members, thus forming a sealed void between at least two of the conductive members, the sealed void spanning at least 50% of the distance between the two conductive members (Fig.16).